



FPAB30BH60

Smart Power Module(SPM®) for Front-End Rectifier

General Description

FPAB30BH60 is an advanced smart power module(SPM®) of PFC(Power Factor Correction) that Fairchild has newly developed and designed mainly targeting mid-power application especially for an air conditioners. It combines optimized circuit protection and drive IC matched to high frequency switching IGBTs. System reliability is further enhanced by the integrated under-voltage lock-out and over-current protection function.

Features

- Low thermal resistance due to Al_2O_3 -DBC substrate
- 600V-30A 1-phase IGBT PWM semi-converter including a drive IC for gate driving and protection
- Typical switching frequency of 20kHz
- Isolation rating of 2500Vrms/min.

Applications

- AC 85V ~ 264V single-phase front-end rectifier

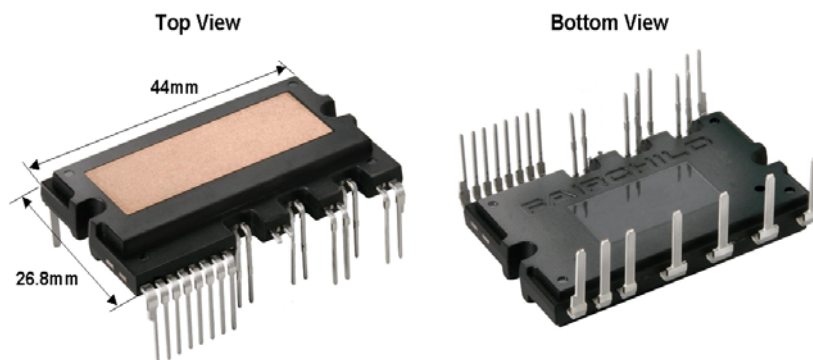


Fig. 1.

Integrated Power Functions

- PFC converter for single-phase AC/DC power conversion (Please refer to Fig. 3)

Integrated Drive, Protection and System Control Functions

- For IGBTs: Gate drive circuit, Overcurrent circuit protection (OC), Control supply circuit under-voltage (UV) protection
- Fault signaling: Corresponding to a UV fault
- Input interface: 5V CMOS/LSTTL compatible, Schmitt trigger input

Pin Configuration

Top View

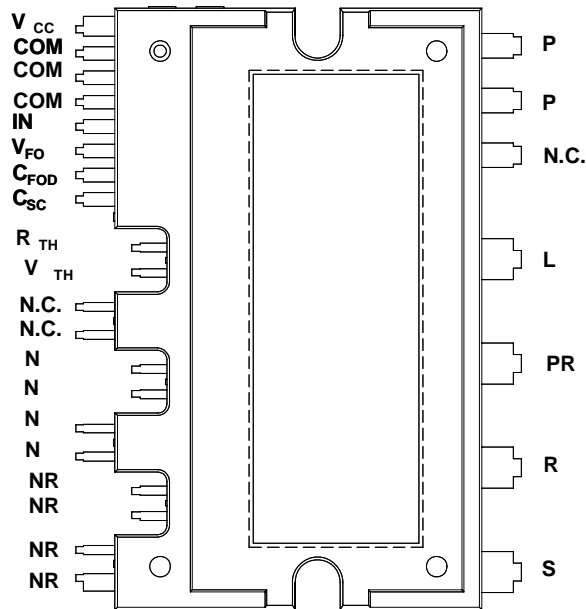


Fig. 2.

Pin Descriptions

Pin Number	Pin Name	Pin Description
1	V _{CC}	Common Bias Voltage for IC and IGBTs Driving
2,3,4	COM	Common Supply Ground
5	IN _(R)	Signal Input for Low-side R-phase IGBT
6	V _{FO}	Fault Output
7	C _{FOD}	Capacitor for Fault Output Duration Time Selection
8	C _{SC}	Capacitor (Low-pass Filter) for Over Current Detection
9	R _(TH)	NTC Thermistor terminal
10	V _(TH)	NTC Thermistor terminal
11,12	N.C	No Connection
13~16	N	IGBT emitter
17~20	N _R	Negative DC-Link of Rectifier
21,22	P	Positive Rail of DC-Link
23	N.C	No Connection
24	L	Reactor connection pin
25	P _R	Positive DC-Link of Rectifier
26	R	AC input for R-phase
27	S	AC input for S-phase

* 11th and 12th pins are cut. Please refer to package outline drawings for more detail.

Internal Equivalent Circuit and Input/Output Pins

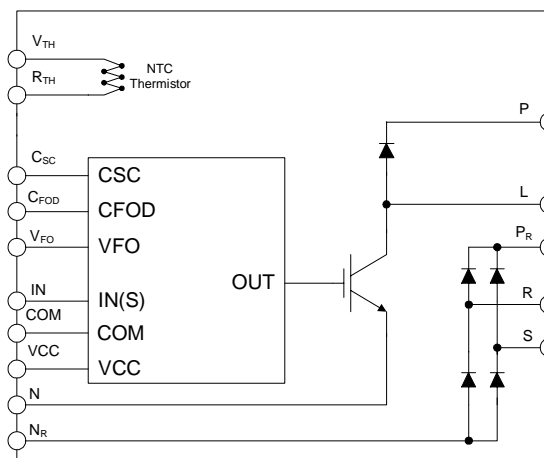


Fig. 3.

Package Marking & Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FPAB30BH60	FPAB30BH60	SPM27-1A	-	-	10

Absolute Maximum Ratings ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)**Converter Part**

Item	Symbol	Condition	Rating	Unit
Supply Voltage	V_i	Applied between R-S	264	V_{RMS}
Supply Voltage (Surge)	$V_{i(Surge)}$	Applied between R-S	500	V
Output Voltage	V_{PN}	Applied between P- N	450	V
Output Voltage (Surge)	$V_{PN(Surge)}$	Applied between P- N	500	V
Collector-emitter Voltage	V_{CES}		600	V
Input Current (100% Load)	I_i	$T_C < 95^\circ\text{C}$, $V_i=220\text{V}$, $V_{PN}= 390\text{V}$, $V_{PWM}=20\text{kHz}$	25	A
Input Current (125% Load)	$I_{i(125\%)}$	$T_C < 95^\circ\text{C}$, $V_i=220\text{V}$, $V_{PN}= 390\text{V}$, $V_{PWM}=20\text{kHz}$, 1min Non-repetitive	30	A
Collector Dissipation	P_C	$T_C = 25^\circ\text{C}$ per One IGBT	169	W
Operating Junction Temperature	T_J	(Note 1)	-20 ~ 150	$^\circ\text{C}$

Note

1. The maximum junction temperature rating of the power chips integrated within the SPM® is 150°C ($@T_C \leq 100^\circ\text{C}$). However, to insure safe operation of the SPM®, the average junction temperature should be limited to $T_{J(ave)} \leq 125^\circ\text{C}$ ($@T_C \leq 100^\circ\text{C}$)

Control Part

Item	Symbol	Condition	Rating	Unit
Control Supply Voltage	V_{CC}	Applied between V_{CC} - COM	20	V
Input Signal Voltage	V_{IN}	Applied between IN - COM	-0.3~5.5	V
Fault Output Supply Voltage	V_{FO}	Applied between V_{FO} - COM	-0.3~ $V_{CC}+0.3$	V
Fault Output Current	I_{FO}	Sink Current at V_{FO} Pin	5	mA
Current Sensing Input Voltage	V_{SC}	Applied between C_{SC} - COM	-0.3~ $V_{CC}+0.3$	V

Total System

Item	Symbol	Condition	Rating	Unit
Module Case Operation Temperature	T_C		-20 ~ 100	$^\circ\text{C}$
Storage Temperature	T_{STG}		-40 ~ 125	$^\circ\text{C}$
Isolation Voltage	V_{ISO}	60Hz, Sinusoidal, AC 1 minute, Connection Pins to DBC	2500	V_{rms}

Thermal Resistance

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Junction to Case Thermal Resistance (Referenced to PKG center)	$R_{\theta(j-c)Q}$	IGBT	-	-	0.74	$^\circ\text{C}/\text{W}$
	$R_{\theta(j-c)F}$	FRD	-	-	1.44	$^\circ\text{C}/\text{W}$
	$R_{\theta(j-c)R}$	Rectifier	-	-	2.07	$^\circ\text{C}/\text{W}$

Note :

2. For the measurement point of case temperature(T_C), please refer to Fig. 2.

Electrical Characteristics ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)**Converter Part**

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
IGBT saturation voltage	$V_{CE(sat)}$	$V_{CC} = 15\text{V}$, $V_{IN} = 5\text{V}$; $I_C = 30\text{A}$	-	2.0	2.8	V
FRD forward voltage	V_{FF}	$I_F = 30\text{A}$	-	1.8	2.5	V
Rectifier forward voltage	V_{FR}	$I_F = 30\text{A}$	-	1.2	1.5	V
Peak surge current	I_{FSM}	Non-repetitive, 60Hz single half-sine wave	200	-	-	A
Switching Times	t_{ON}	$V_{PN} = 400\text{V}$, $V_{CC} = 15\text{V}$, $I_C = 30\text{A}$ $V_{IN} = 0\text{V} \leftrightarrow 5\text{V}$, Inductive Load (Note 3)	-	650	-	ns
	$t_{C(ON)}$		-	400	-	ns
	t_{OFF}		-	620	-	ns
	$t_{C(OFF)}$		-	200	-	ns
	t_{rr}		-	60	-	ns
	I_{rr}		-	3.5	-	A
Collector - emitter Leakage Current	I_{CES}	$V_{CE} = V_{CES}$	-	-	250	μA

Note

3. t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Fig. 4

Control Part

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Quiescent V_{CC} Supply Current	I_{QCCL}	$V_{CC} = 15\text{V}$, $I_N = 0\text{V}$ $V_{CC} - \text{COM}$	-	-	26	mA
Fault Output Voltage	V_{FOH}	$V_{SC} = 0\text{V}$, V_{FO} Circuit: 4.7k Ω to 5V Pull-up	4.5	-	-	V
	V_{FOL}	$V_{SC} = 1\text{V}$, V_{FO} Circuit: 4.7k Ω to 5V Pull-up	-	-	0.8	V
Over Current Trip Level	$V_{SC(ref)}$	$V_{CC} = 15\text{V}$	0.45	0.5	0.55	V
Supply Circuit Under-Voltage Protection	UV_{CCD}	Detection Level	10.7	11.9	13.0	V
	UV_{CCR}	Reset Level	11.2	12.4	13.2	V
Fault-out Pulse Width	t_{FOD}	$C_{FOD} = 33\text{nF}$ (Note 4)	1.4	1.8	2.0	ms
ON Threshold Voltage	$V_{IN(ON)}$	Applied between IN - COM	3.0	-	-	V
OFF Threshold Voltage	$V_{IN(OFF)}$		-	-	0.8	V
Resistance of Thermistor	R_{TH}	@ $T_C = 25^\circ\text{C}$ (Note Fig. 9)	-	50	-	k Ω
		@ $T_C = 100^\circ\text{C}$ (Note Fig. 9)	-	2.99	-	k Ω

Note

4. The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation : $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}[F]$

Electrical Characteristics

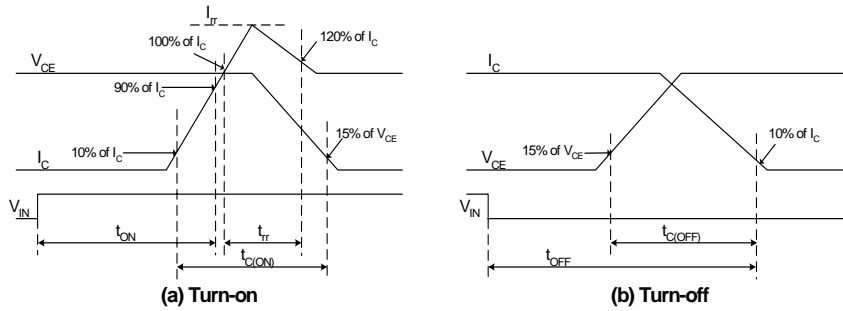


Fig. 4. Switching Time Definition

Mechanical Characteristics and Ratings

Item	Condition	Limits			Units
		Min.	Typ.	Max.	
Mounting Torque	Mounting Screw: - M3 Recommended 0.62N•m	0.51	0.62	0.72	N•m
Device Flatness	Note Fig. 5	0	-	+120	μm
Weight		-	15.00	-	g

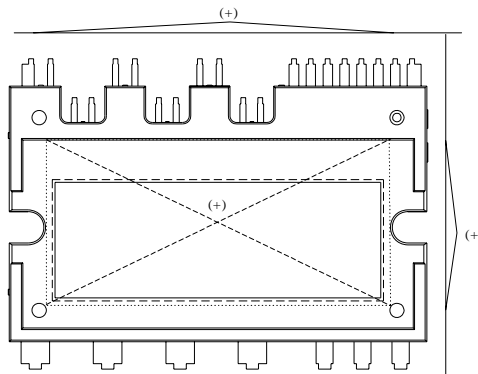
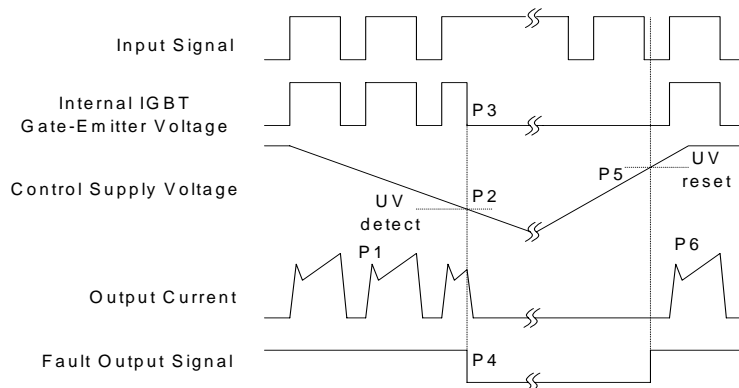


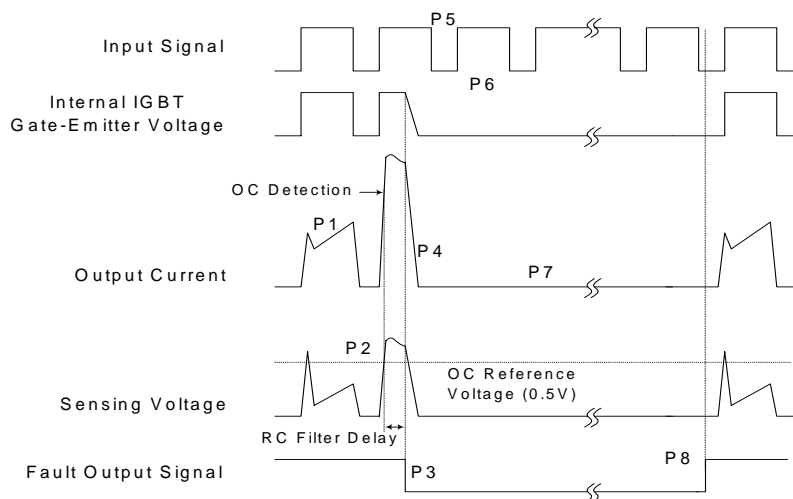
Fig. 5. Flatness Measurement Position

Time Charts of SPMs Protective Function



- P1 : Normal operation - IGBT ON and conducting current
- P2 : Under voltage detection
- P3 : IGBT gate interrupt
- P4 : Fault signal generation
- P5 : Under voltage reset
- P6 : Normal operation - IGBT ON and conducting current

Fig. 6. Under-Voltage Protection



- P1 : Normal operation - IGBT ON and conducting current
- P2 : Over current detection
- P3 : IGBT gate interrupt / Fault signal generation
- P4 : IGBT is slowly turned off
- P5 : IGBT OFF signal
- P6 : IGBT ON signal - but IGBT cannot be turned on during the fault Output activation
- P7 : IGBT OFF state
- P8 : Fault Output reset and normal operation start

Fig. 7. Over Current Protection

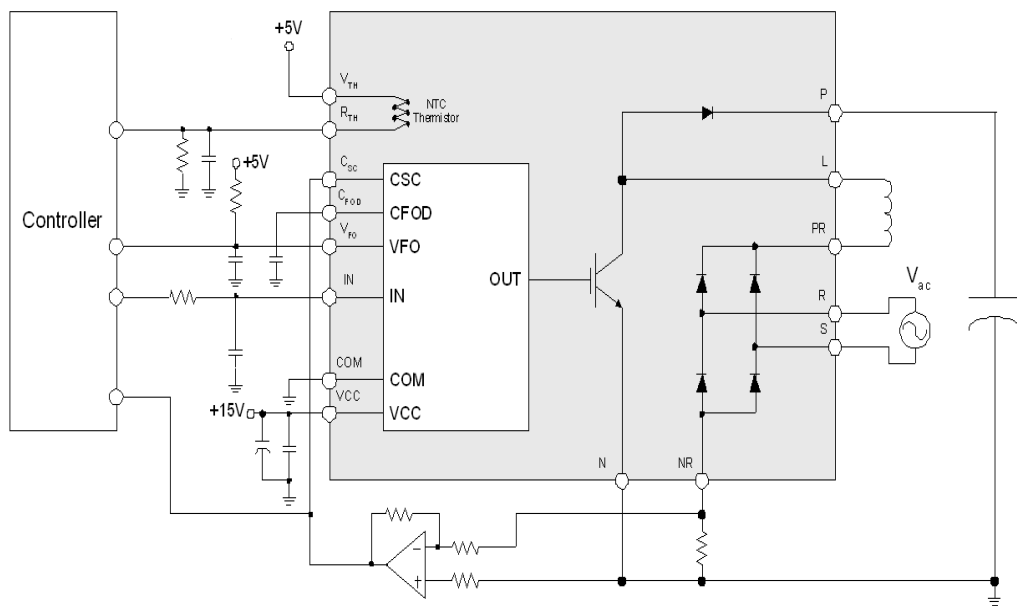


Fig. 8. Application Example

R-T Graph

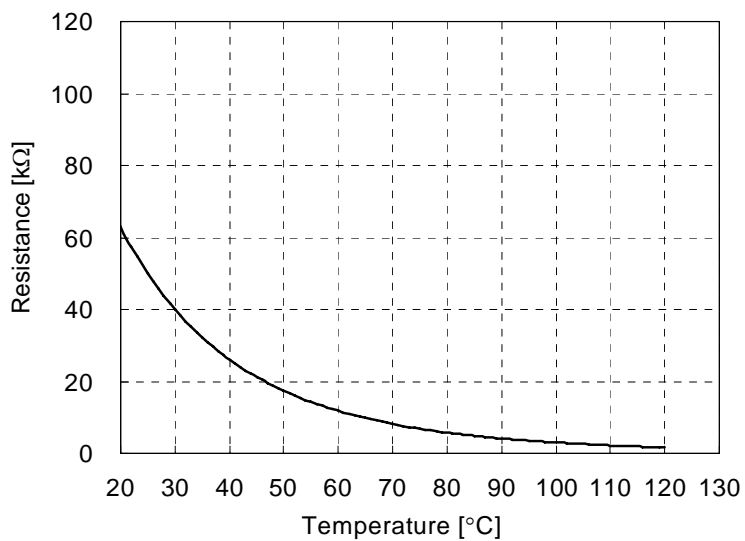
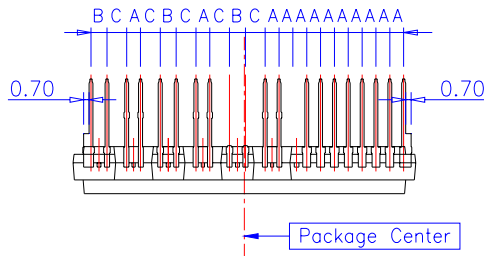


Fig. 9. R-T Curve of the Built-in Thermistor

Detailed Package Outline Drawings

FPAB30BH60 Smart Power Module (SPM®)

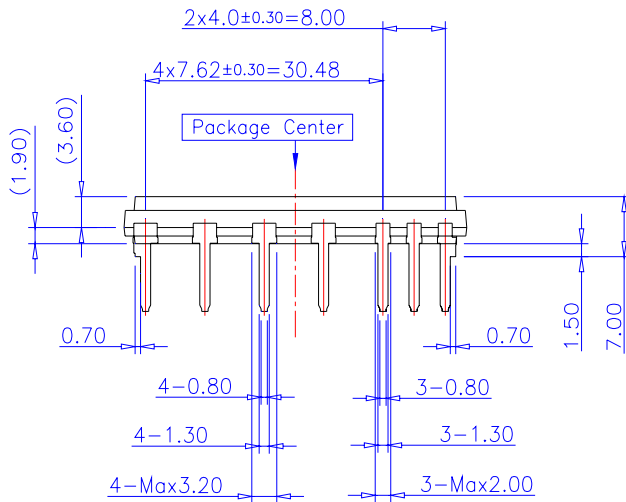
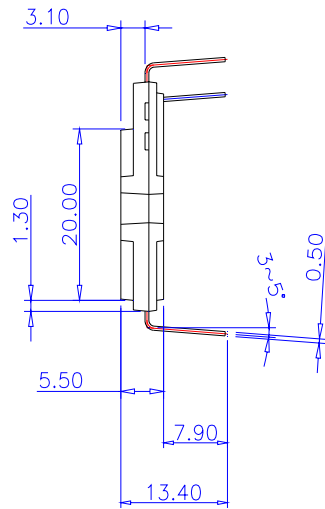
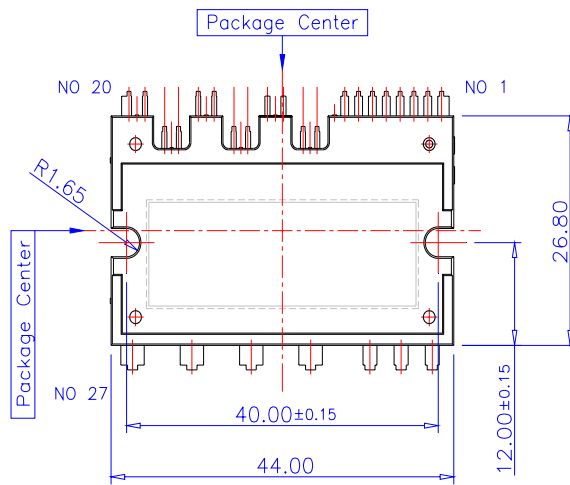


Lead Pitch : ± 0.30

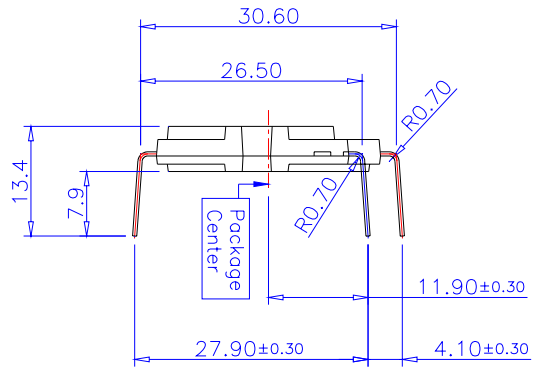
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B : 2.050

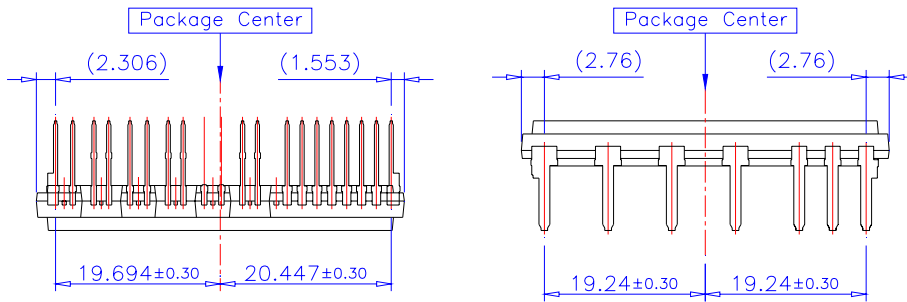
C : 2.531



Detailed Package Outline Drawings



Lead Forming Dimension

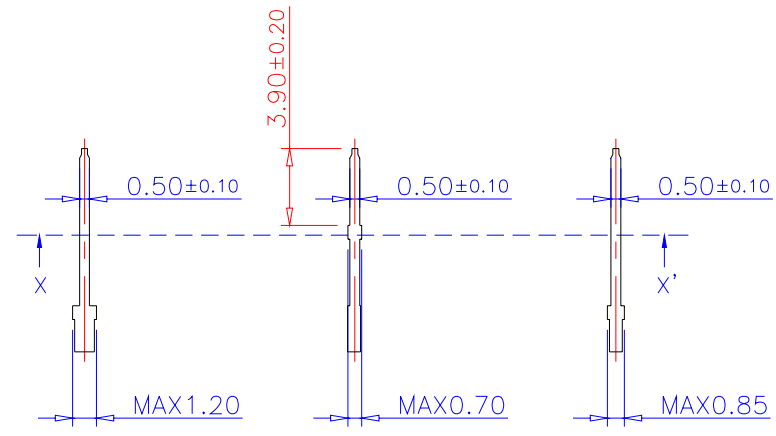
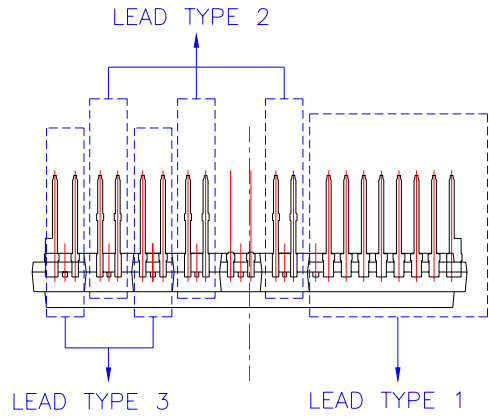


PKG Center to Lead Distance

Detailed Package Outline Drawings

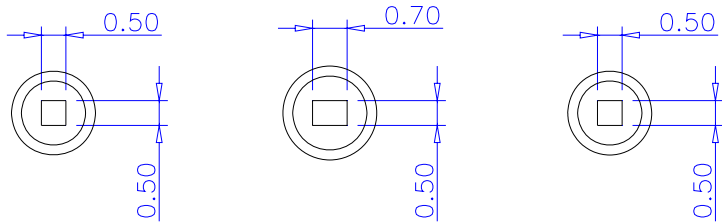
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DETAIL LEAD




LEAD TYPE 1 LEAD TYPE 2 LEAD TYPE 3

SCALE 2 : 1



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